

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Application of: Fabrice LETERTRE *et al.*

Application No.:

Group Art Unit:

Filing Date: Concurrently herewith

Examiner:

For: WAFER AND METHOD OF PRODUCING A  
SUBSTRATE BY TRANSFER OF A LAYER  
THAT INCLUDES FOREIGN SPECIES

Attorney Docket No.: 4717-7400

**INFORMATION DISCLOSURE STATEMENT**

**MS PATENT APPLICATION**

Commissioner for Patents

P.O. Box 1450

Arlexandria, Virginia 22313-1450

Sir:

Pursuant to Applicant's duty of disclosure under 37 C.F.R. § 1.56, enclosed are copies of four (4) references listed on the enclosed Form PTO-1449 for the Examiner's review. Also enclosed is a copy of the International Search Report from the priority foreign application on which the references were cited. It is respectfully requested that the references be made of record in this application by the Examiner's completion and return of the attached Form PTO-1449.

No fee is believed to be due for the submission of the references. Should any fees be required, however, please charge such fees to Winston & Strawn Deposit Account No. 50-1814. A copy of this sheet is enclosed for accounting purposes.

Respectfully submitted,

October 6, 2003

Date

E. Bradley Gould (Reg. No. 41,792)  
For: Allan A. Fanucci (Reg. No. 30,256)

**WINSTON & STRAWN**  
**Customer No. 28765**

202-371-5771

<b>LIST OF REFERENCES CITED BY APPLICANT</b> <b>Form PTO-1449</b> <i>(Use several sheets if necessary)</i>	ATTY. DOCKET NO.: <b>4717-7400</b>	APPLICATION NO.: 
	APPLICANT: <b>Fabrice LETERTRE <i>et al.</i></b>	
Sheet 1 of 1	FILING DATE: <b>6 October 2003</b>	GROUP:

### U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	CITE NO.	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

### FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
	A	WO 02/37556	05/2002	PCT				

### OTHER REFERENCES *(Including Author, Title, Date, Pertinent Pages, Etc.)*

	B	Jalaguier <i>et al.</i> , "Transfer of thin InP films onto silicon substrate by proton implantation process," May, 1999
	C	R. Fornari <i>et al.</i> , "Homogeneity of thermally annealed Fe-doped InP wafers," 1997
	D	A. Näser <i>et al.</i> , "Thermal stability of the midgap acceptor rhodium in indium phosphide" 1995

<b>EXAMINER</b>	<b>DATE CONSIDERED</b>
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**\*EXAMINER:** Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.